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TCAD simulations and beam tests: measuring the electric field in irradiates sensors

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Beam test data and simulations can make accessible the electric field profile of silicon sensors. Different bulk materials, irradiation and annealing scenarios can be contrasted thanks to the charge profile technique (e.g.: T. Lari and C. Troncon, IEEE TNS, VOL. 53, NO. 5, OCTOBER 2006; V. Chiochia, IEEE TNS, VOL. 52, NO. 4, AUGUST 2005)
High pointing resolution telescopes and detailed TCAD simulations are needed to complete this task.
I will present a project for beam tests and simulations campaigns.

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